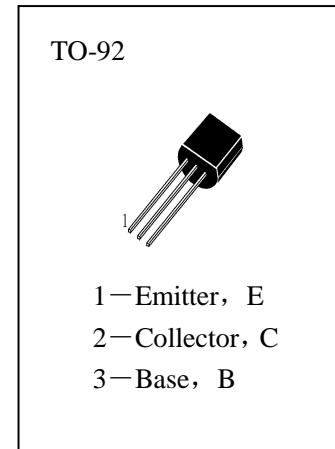


KI SEMICONDUCTOR**C1815****■ AUDIO FREQUENCY AMPLIFIER****HIGH FREQUENCY OSC****■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**T_{stg}—Storage Temperature..... -55~150°CT_j—Junction Temperature..... 150°CP_C—Collector Dissipation..... 400mWV_{CBO}—Collector-Base Voltage..... 60VV_{CEO}—Collector-Emitter Voltage..... 50VV_{EBO}—Emitter-Base Voltage..... 5VI_C—Collector Current..... 150mA**■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)**

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|--------------------|---------------------------------------|-----|-----|-----|------|---|
| I _{CBO} | Collector Cut-off Current | | | 100 | nA | V _{CB} =60V, I _E =0 |
| I _{EBO} | Emitter Cut-off Current | | | 100 | nA | V _{EB} =5V, I _C =0 |
| H _{FE(1)} | DC Current Gain | 70 | | 700 | | V _{CE} =6V, I _C =2mA |
| H _{FE(2)} | | 25 | | | | V _{CE} =6V, I _C =150mA |
| V _{CESAT} | Collector- Emitter Saturation Voltage | | | 250 | mV | I _C =100mA, I _B =10mA |
| V _{BESAT} | Base-Emitter Saturation Voltage | | | 1.0 | V | I _C =100mA, I _B =10mA |
| BV _{CBO} | Collector-Base Breakdown Voltage | 60 | | | V | I _C =100 μ A, I _E =0 |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | 50 | | | V | I _C =1mA, I _B =0 |
| BV _{EBO} | Emitter-Base Breakdown Voltage | 5 | | | V | I _E =100 μ A, I _C =0 |
| f _T | Current Gain-Bandwidth Product | 80 | | | MHz | V _{CE} =10V, I _C =1mA |

■ hfe Classification

| O | Y | GR | BL |
|--------|---------|---------|---------|
| 70—140 | 120—240 | 200—400 | 350—700 |

KI SEMICONDUCTOR

NPN SILICON TRANSISTOR

C1815

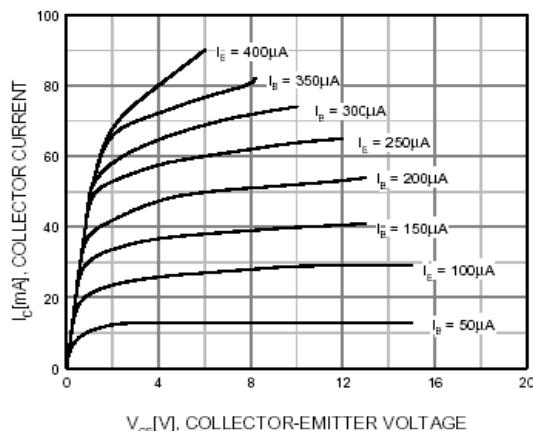


Figure 1. Static Characteristic

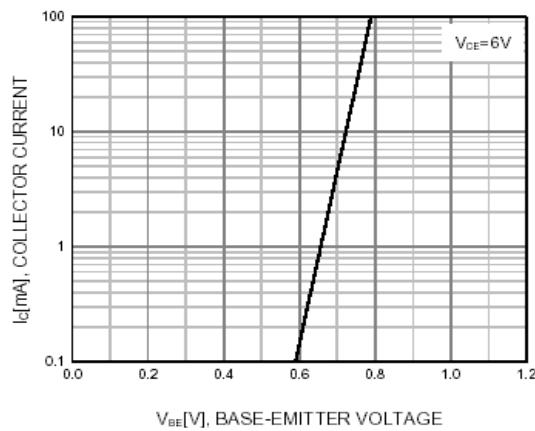


Figure 2. Transfer Characteristic

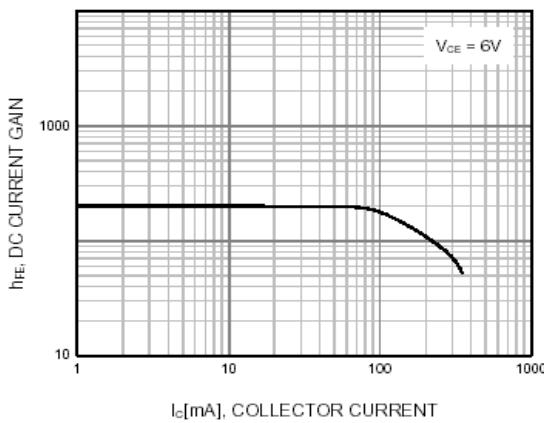


Figure 3. DC current Gain

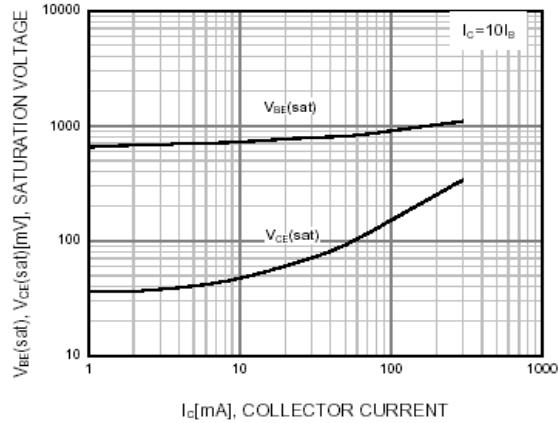


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

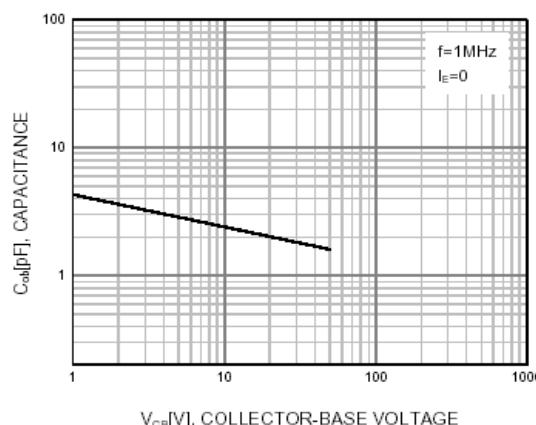


Figure 5. Output Capacitance

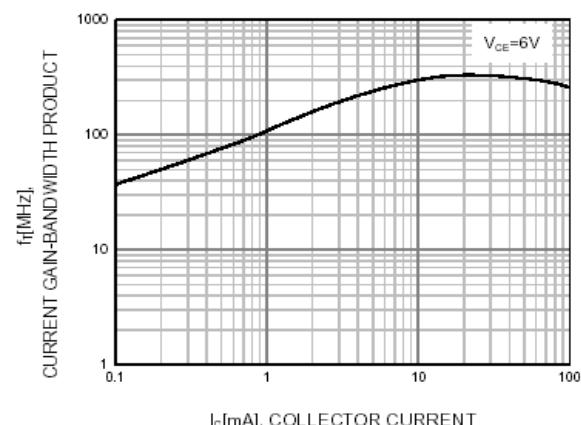


Figure 6. Current Gain Bandwidth Product